Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 40 A



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PRIMARY CHARACTERISTICS				
I _{T(AV)}	25 A			
V _{DRM} /V _{RRM}	1200 V			
V _{TM}	1.6 V			
I _{GT}	35 mA			
TJ	-40 °C to 140 °C			
Package	3L TO-220AB			
Circuit configuration	Single SCR			

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 140 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-40TTS12... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 140 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	25	А		
I _{RMS}		40	A		
V _{RRM} /V _{DRM}		1200	V		
I _{TSM}		350	А		
V _T	$T_J = 25 \ ^{\circ}C$	1.6	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		-40 to +140	°C		

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	TJ ℃
VS-40TTS12-M3	1200	1200	-25 to +140



VS-40TTS12-M3



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ABSOLUTE MAXIMUM RATING	5				
PARAMETER	SYMBOL	TEST CON	NDITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 93 ^{\circ}{\rm C}, 180^{\circ} {\rm conduct}$	tion half sine wave	25	
Maximum RMS on-state current	I _{RMS}			40	А
Maximum peak, one-cycle	l	10 ms sine pulse, rated V	/ _{RRM} applied	300	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volt	age reapplied	350	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V	/ _{RRM} applied	450	A ² s
Maximum i-t for fusing	1-1	10 ms sine pulse, no volt	age reapplied	630	A-S
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10 ms, no volta	t = 0.1 to 10 ms, no voltage reapplied		A²√s
Maximum on-state voltage	V _{TM}	80 A, T _J = 25 °C		1.6	V
Low level value of on-state slope resistance	r _t	T ₁ = 140 °C		11.4	mΩ
Low level value of threshold voltage	V _{T(TO)}	1) = 140 0		0.96	V
Maximum reverse and direct leakage	1 /1	T _J = 25 °C	V _R = Rated V _{RRM} /V _{DRM}	0.5	
current	I _{RRM} /I _{DRM}	T _J = 140 °C	VR - naleu VRRM/ VDRM	12	
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 $^\circ C$		100	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		200	
Maximum rate of rise of off-state voltage	dV/dt	T _J = T _J max., linear to 80 °C, V _{DRM} = R _g - k = Open		500	V/µs
Maximum rate of rise of turned-on current	dl/dt			150	A/µs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	vv
Maximum peak positive gate current	+ I _{GM}		1.5	А
Maximum peak negative gate voltage	- V _{GM}		10	V
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	35	mA
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	1.3	V
Maximum DC gate voltage not to trigger	V _{GD}	T _{.I} = 140 °C, V _{DBM} = Rated value	0.2	
Maximum DC gate current not to trigger	I _{GD}	$T_{\rm J} = 140$ O, $v_{\rm DRM} = hated value$	1.5	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T _{.1} = 140 °C	4	μs
Typical turn-off time	t _q	1j = 140 C	110	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL TEST CONDITIONS		VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to 140	°C	
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	0.8		
Maximum thermal resistance, junction to ambient		R _{thJA}		60	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	oz.	
Mounting torque	minimum			6 (5)	kgf∙cm	
Mounting torque	maximum			12 (10)	(lĎf ⋅ in)	
Marking device			Case style 3L TO-220AB	40T	rS12	

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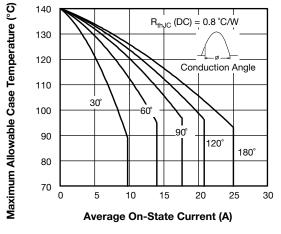


Fig. 1 - Current Rating Characteristics

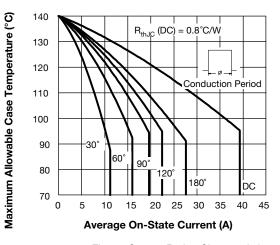


Fig. 2 - Current Rating Characteristics

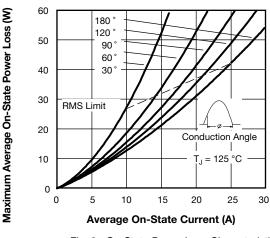


Fig. 3 - On-State Power Loss Characteristics

70 DC 180 60 120 90 50 60 ° 30 40 RMS Limit 30 20 **Conduction Period** 10 T_J = 125 °C 0 0 10 20 30 40

Maximum Average On-State Power Loss (W)

Average On-State Current (A)

Fig. 4 - On-State Power Loss Characteristics

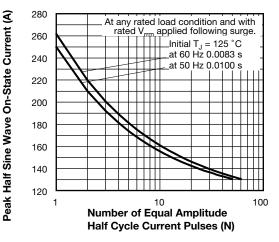


Fig. 5 - Maximum Non-Repetitive Surge Current

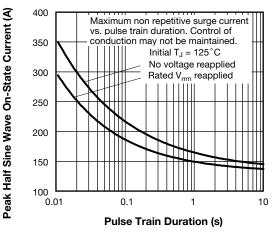


Fig. 6 - Maximum Non-Repetitive Surge Current

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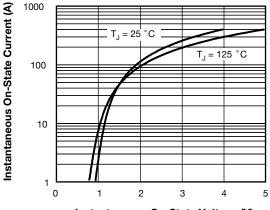
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VS-40TTS12-M3

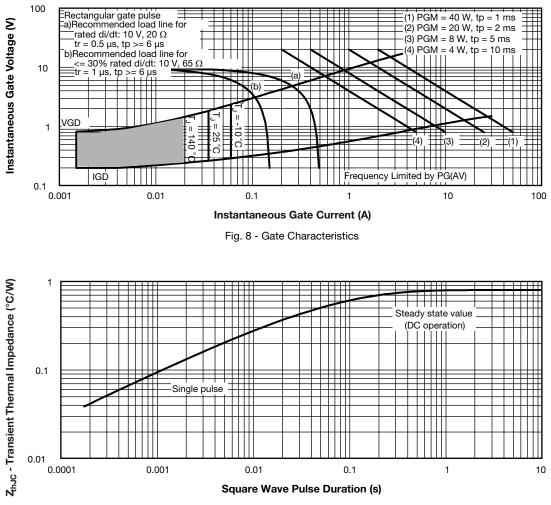
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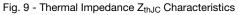




Instantaneous On-State Voltage (V)

Fig. 7 - On-State Voltage Drop Characteristics





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ORDERING INFORMATION TABLE

Device code	VS-	40	т	т	s	12	-M3
		(2)	(3)	4	(5)	(6)	(7)
		\bigcirc	\bigcirc	\bigcirc	\cup	\bigcirc	\mathbf{O}
	<u> </u>		•	niconduc	•	duct	
	2 -			ng, RMS			
	3 -			iguration	1:		
		T =	single th	nyristor			
	4 -	- Pac	kage:				
		T = 1	TO-220				
	5 -	- Тур	e of silic	con:			
		S =	standar	d recove	ery rectif	ier	
	6 -	· Volt	age rati	ng (12 =	1200 V)	
	7 -	. Envi	ronmen	tal digit:			
		-M3	= halog	en-free,	RoHS-c	ompliar	nt, and t

ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-40TTS12-M3	50	1000	Antistatic plastic tubes			

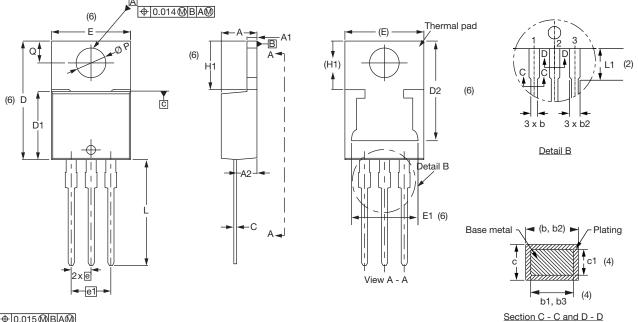
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028



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3L TO-220AB

DIMENSIONS in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

Conforms to JEDEC [®]	outline	TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Ш	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1

⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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